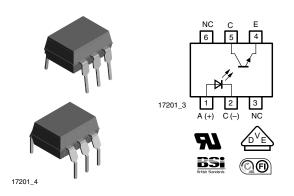
TCDT1100, TCDT1100G

Vishay Semiconductors



Optocoupler, Phototransistor Output



DESCRIPTION

The TCDT1100, TCDT1100G series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6 pin plastic dual inline package. The base of the phototransistor is not connected providing noise immunity.

VDE STANDARDS

These couplers perform safety functions according to the following equipment standards:

- DIN EN 60747-5-5 (VDE0884) Optocoupler for electrical safety requirements
- IEC 60950/EN 60950

Office machines (applied for reinforced isolation for mains voltage $\leq 400~V_{RMS})$

• VDE0804

Telecommunication apparatus and data processing

• IEC 60065

Safety for mains-operated electronic and related household apparatus

FEATURES

- Isolation test voltage 5000 V_{RMS}
- High common mode rejection
- No base terminal connection for improved noise immunity
- CTR offered in 4 groups
- Thickness though insulation $\ge 0.4 \text{ mm}$
- Creepage current resistance according to VDE0303/ IEC 60112 comparative tracking index: CTI ≥ 275
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
 - for appl. class I IV at mains voltage $\leq 300~V$
 - for appl. class I III at mains voltage ≤ 600 V according to DIN EN 60747-5-5

AGENCY APPROVALS

- UL1577, file no. E52744, double protection
- BSI IEC 60950; IEC 60065 pending
- DIN EN 60747-5-5 (VDE0884)
- FIMKO

ORDER INFORMATION					
PART	REMARKS				
TCDT1100	CTR > 40 %, DIP-6				
TCDT1101	CTR 40 % to 80 %, DIP-6				
TCDT1102	CTR 63 % to 125 %, DIP-6				
TCDT1103	CTR 100 % to 200 %, DIP-6				
TCDT1100G	CTR > 40 %, DIP-6, 400 mil				
TCDT1101G	CTR 40 % to 80 %, DIP-6, 400 mil				
TCDT1102G	CTR 63 % to 125 %, DIP-6, 400 mil				
TCDT1103G	CTR 100 % to 200 %, DIP-6, 400 mil				

Note

• G = leadform 10.16 mm; G is not marked on the body.

Pb-free

RoHS

COMPLIANT



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PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT	i			
Reverse voltage		V _R	5	V
Forward current		I _F	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	3	А
Power dissipation		P _{diss}	70	mW
Junction temperature		Tj	125	°C
OUTPUT				
Collector emitter voltage		V _{CEO}	32	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		Ι _C	50	mA
Collector peak current	$t_p/T=0.5,t_p\leq 10\ ms$	I _{CM}	100	mA
Power dissipation		P _{diss}	70	mW
Junction temperature		Tj	125	°C
COUPLER				
Isolation test voltage (RMS)		V _{ISO}	5000	V _{RMS}
Total power dissipation		P _{tot}	200	mW
Ambient temperature range		T _{amb}	- 55 to + 110	°C
Storage temperature range		T _{stg}	- 55 to + 125	°C
Soldering temperature ⁽²⁾	2 mm from case, t \leq 10 s	T _{sld}	260	°C

Notes

⁽¹⁾ Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTCS ⁽¹⁾ ($T_{amb} = 25 \degree C$, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT							
Forward voltage	I _F = 50 mA	V _F		1.25	1.6	V	
Junction capacitance	V _R = 0, f = 1 MHz	Cj		50		pF	
OUTPUT							
Collector emitter voltage	I _C = 1 mA	V _{CEO}	32			V	
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7			V	
Collector ermitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0, E = 0$	I _{CEO}		200		nA	
COUPLER							
Collector emitter saturation voltage	$I_{\rm F} = 10 \text{ mA}, I_{\rm C} = 1 \text{ mA}$	V _{CEsat}			0.3	V	
Cut-off frequency	$V_{CE} = 5 \text{ V}, \text{ I}_{F} = 10 \text{ mA},$ $R_{L} = 100 \Omega$	f _c		110		kHz	
Coupling capacitance	f = 1 MHz	C _k		0.6		pF	

Note

⁽¹⁾ Minimum and maximum values are testing requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.



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CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
		TCDT1100	CTR	40			%	
		TCDT1100G	CTR				%	
		TCDT1101	CTR	40		80	%	
1.4	V 5.V 10 mA	TCDT1101G	CTR				%	
I _C /I _F	V _{CE} = 5 V, I _F = 10 mA	TCDT1102	CTR	63		125	%	
		TCDT1102G	CTR			120	%	
		TCDT1103	CTR	100		000	%	
		TCDT1103G	CTR	100		200	%	

MAXIMUM SAFETY RATINGS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward current		I _F			130	mA		
OUTPUT								
Power dissipation		P _{diss}			265	mW		
COUPLER								
Rated impulse voltage		V _{IOTM}			6	kV		
Safety temperature		T _{si}			150	°C		

Note

• According to DIN EN 60747-5-5. This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t _{test} = 1 s	V_{pd}	1.6			kV	
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$ (see figure 1)	V _{IOTM}	6			kV	
		V _{pd}	1.3			kV	
Insulation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω	
	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 100 ^{\circ}\text{C}$	R _{IO}	10 ¹¹			Ω	
	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹			Ω	

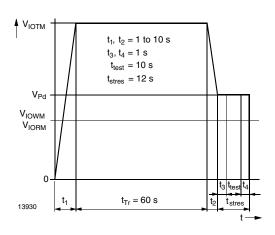


Fig. 1 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC60747



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SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ R}_{L} = 100 \Omega$, (see figure 2)	t _d		4		μs	
Rise time	$V_S = 5 V$, $I_C = 5 mA$, $R_L = 100 \Omega$, (see figure 2)	tr		7		μs	
Fall time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ R}_{L} = 100 \Omega$, (see figure 2)	t _f		6.7		μs	
Storage time	$V_S = 5 \text{ V}, \text{ I}_C = 5 \text{ mA}, \text{ R}_L = 100 \Omega$, (see figure 2)	t _s		0.3		μs	
Turn-on time	$V_S = 5 V$, $I_C = 5 mA$, $R_L = 100 \Omega$, (see figure 2)	t _{on}		11		μs	
Turn-off time	$V_{S} = 5 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ R}_{L} = 100 \Omega$, (see figure 2)	t _{off}		7		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 10 \text{ mA}, R_L = 1 \text{ k}\Omega$, (see figure 3)	t _{on}		25		μs	
Turn-off time	$V_S = 5 V$, $I_C = 10 mA$, $R_L = 1 k\Omega$, (see figure 3)	t _{off}		42.5		μs	

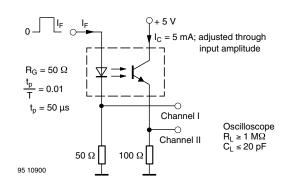


Fig. 2 - Test Circuit, Non-Saturated Operation

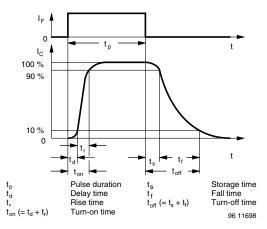


Fig. 4 - Switching Times

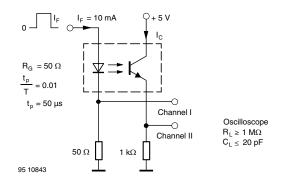


Fig. 3 - Test Circuit, Saturated Operation

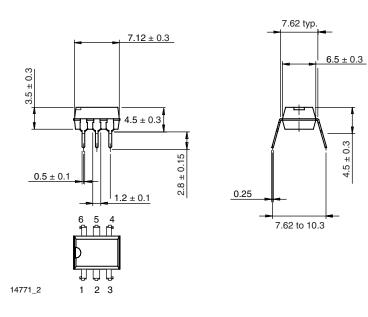
TCDT1100, TCDT1100G

Vishay Semiconductors Optocoupler, Phototransistor Output

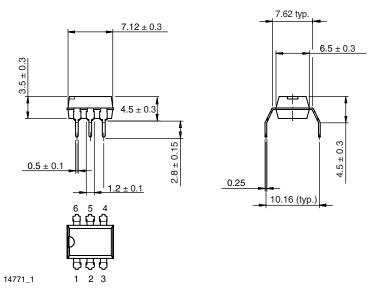


PACKAGE DIMENSIONS in millimeters

DIP-6



DIP-6, 400 mil



PACKAGE MARKING





Vishay

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